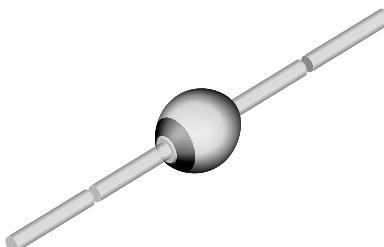


Features

- Glass passivated junction
- Hermetically sealed package
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



949539

Applications

High voltage rectification diode

Efficiency diode in horizontal deflection circuits

Mechanical Data

Case: SOD-57 Sintered glass case

Terminals: Plated axial leads, solderable per
MIL-STD-750, Method 2026

Polarity: Color band denotes cathode end

Mounting Position: Any

Weight: approx. 369 mg

Parts Table

Part	Type differentiation	Package
BY448	$V_R = 1500 \text{ V}$; $I_{FAV} = 2 \text{ A}$	SOD-57
BY458	$V_R = 1200 \text{ V}$; $I_{FAV} = 2 \text{ A}$	SOD-57

Absolute Maximum Ratings

 $T_{amb} = 25 \text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Part	Symbol	Value	Unit
Reverse voltage	see electrical characteristics	BY448	$V_R = V_{RRM}$	1500	V
		BY458	$V_R = V_{RRM}$	1200	V
Peak forward surge current	$t_p = 10 \text{ ms}$, half sinewave		I_{FSM}	30	A
Average forward current			I_{FAV}	2	A
Junction temperature			T_j	140	$^{\circ}\text{C}$
Storage temperature range			T_{stg}	- 55 to + 175	$^{\circ}\text{C}$
Non repetitive reverse avalanche energy	$I_{(BR)R} = 0.4 \text{ A}$		E_R	10	mJ

Maximum Thermal Resistance

 $T_{amb} = 25 \text{ }^{\circ}\text{C}$, unless otherwise specified

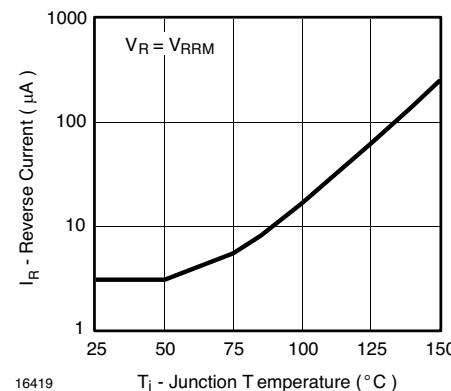
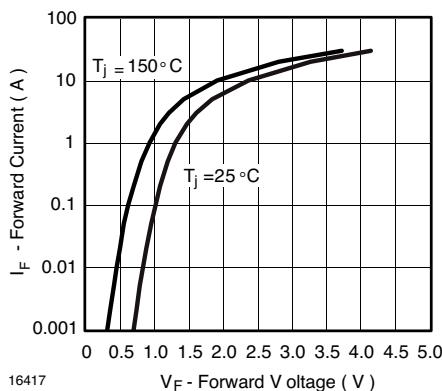
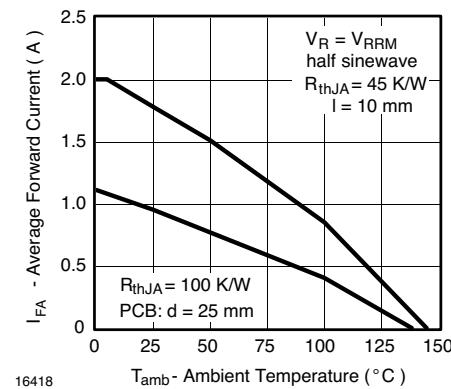
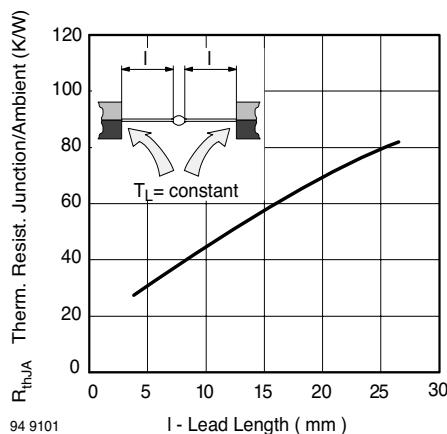
Parameter	Test condition	Symbol	Value	Unit
Junction ambient	$I = 10 \text{ mm}, T_L = \text{constant}$	R_{thJA}	45	K/W
	on PC board with spacing 25 mm	R_{thJA}	100	K/W

Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Forward voltage	$I_F = 3 \text{ A}$	V_F			1.6	V
Reverse current	$V_R = V_{RRM}$	I_R			3	μA
	$V_R = V_{RRM}, T_j = 140^{\circ}\text{C}$	I_R			140	μA
Total reverse recovery time	$I_F = 1 \text{ A}, -d_iF/d_t = 0.05 \text{ A}/\mu\text{s}$	t_{rr}			20	μs
Reverse recovery time	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, i_R = 0.25 \text{ A}$	t_{rr}			2	μs

Typical Characteristics (Tamb = 25 °C unless otherwise specified)



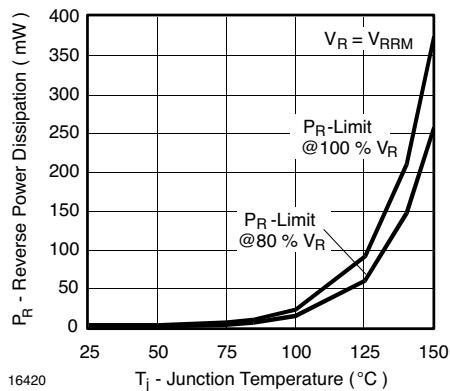


Figure 5. Max. Reverse Power Dissipation vs. Junction Temperature

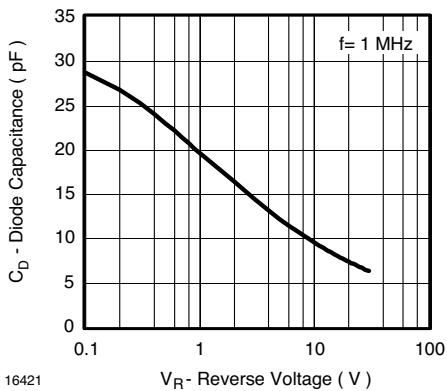


Figure 6. Diode Capacitance vs. Reverse Voltage

Package Dimensions in mm (Inches)

